



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

FUKUDA, Masatoshi et al.

#8/a
2/5/03
Shm Th
Group Art Unit: 2815

Serial No.: 10/020,951

Examiner: LANDAU, M.

Filed: December 19, 2001

P.T.O. Confirmation No.: 8648

For: SEMICONDUCTOR DEVICE AND METHOD FOR FABRICATING THE SAME

AMENDMENT UNDER 37 CFR §1.111

Commissioner for Patents
Washington, D.C. 20231

January 28, 2003

Sir:

In response to the Office Action dated October 1, 2002, please amend the above-identified application as follows:

IN THE CLAIMS:

Please CANCEL claims 5 and 6 without prejudice or disclaimer.

Please AMEND claims as follows:

1. (Amended) A semiconductor device comprising:

a capacitor formed above a semiconductor substrate and including

 a cylindrical-shaped storage electrode,

 a capacitor dielectric film formed on the storage electrode, and

 a plate electrode formed on the capacitor dielectric film,

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